

IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application.

Claims 1-8 (canceled)

1 9. (new) A photoresist laminate comprising:
2 a substrate;
3 a photoresist pattern with a reinforcing section formed by using an exposure and a
4 developing solution,
5 a sublayer film provided between the substrate and the photoresist pattern, the sublayer
6 film being soluble in a developing solution used to form the photoresist pattern; and
7 wherein there is provided in said photoresist pattern line section and a reinforcing section
8 that continues to said line section and that has a greater width than a line width of said line
9 section..

1 10. (new) A method of forming a photoresist laminate according to claim 9, comprising:
2 forming on a substrate a sublayer film that is soluble in a developing solution used in a
3 developing process;
4 forming on the sublayer film a photoresist film;
5 exposing the photoresist film; and
6 developing the photoresist film by the developing solution.

1 11. (new) A method of evaluating a photoresist pattern, comprising:
2 forming on a substrate a photoresist pattern with a reinforcing section, wherein there is
3 provided a line section and a reinforcing section that continues to said line section and that has a
4 greater width than a line width of said line section;
5 providing on the substrate a sublayer film that is soluble in a developing solution used in
6 a developing process;
7 forming on the sublayer film a photoresist film;
8 exposing the photoresist film; and
9 developing the photoresist film by the developing solution, to create an evaluation

10 substrate; and
11 splitting said evaluation substrate in a cross section perpendicular to the lengthwise
12 direction of said line such that it is possible to observe said cross section.

1 12. (new) A method of evaluating a photoresist pattern according to claim 11, wherein when
2 creating said evaluation substrate, a plurality of photoresist patterns with reinforcing sections are
3 formed such that lengthwise directions of line sections are parallel, and locations of reinforcing
4 sections in the lengthwise direction of the line sections are different for adjacent photoresist
5 patterns with reinforcing sections.

1 13. (new) A method of manufacturing a device using a lithographic method that includes a
2 process of forming on a substrate a photoresist pattern having a line section on at least part
3 thereof, said method comprising:
4 forming on a substrate a photoresist pattern with a reinforcing section, wherein there is
5 provided a line section and a reinforcing section that continues to said line section and that has a
6 greater width than a line width of said line section, or a plurality of such reinforcing sections
7 with spaces between themselves;
8 providing on the substrate a sublayer film that is soluble in a developing solution used in
9 a developing process;
10 forming on the sublayer film a photoresist film, exposing the photoresist film; and
11 delveloping the photoresist film by the developing solution.